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MMUN2115LT1G
Digital Transistor(PNP)

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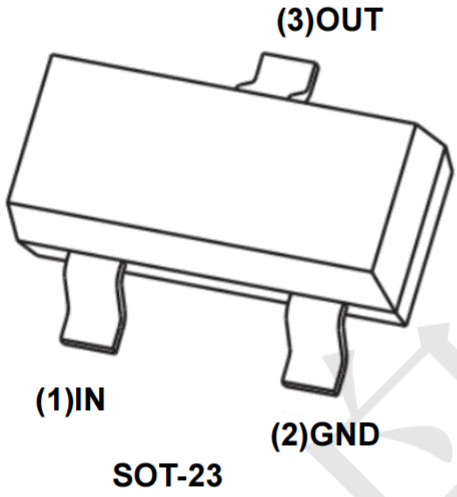
Product Summary

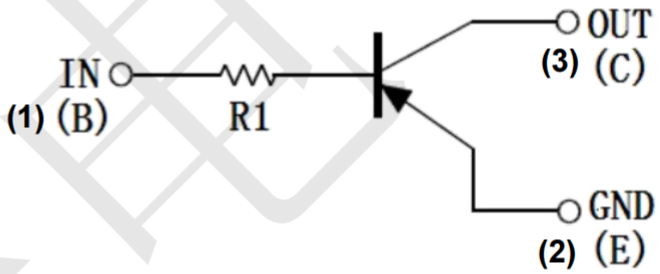
- VCBO = -50V
- VCEO = -50V
- IC = -100mA
- R1 = 10kΩ

Features

- Built-in bias resistors
- making device design easy
- almost completely eliminating parasitic effects

Circuit diagram and pin information





Absolute Maximum Ratings

(Ta=25°C unless otherwise specified)

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	VCBO	-50	V
Collector-Emitter Voltage	VCEO	-50	V
Emitter-Base Voltage	VEBO	-5V	V
Collector current	IC	-100	mA
Power Total Dissipation @ T_A=25ºC	P_D	200	mW
Maximum Operating Junction Temperature	T_J	+150	°C
Storage Temperature Range	TSTG	-55 to +150	°C

Electrical Characteristics

(TA=25°C unless otherwise specified)

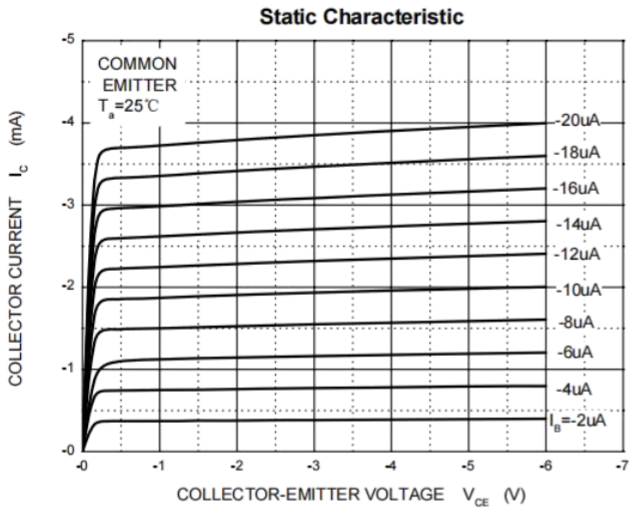
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-50μA,I_E=0	-50	--	--	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-50	--	--	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-50μA,I_C=0	-5	--	--	V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_E=0	--	--	-0.5	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0	--	--	-0.5	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-5mA,I_B=-0.5mA	--	--	-0.3	V
DC current gain	h_{FE}	V_{CE}=-5V,I_C=-1mA	100	250	600	--
Input resistor	R_1		7	10	13	kΩ
Transition frequency	f_T	V_{CE}=-10V,I_E=-5mA, f=100MHz	--	250	--	MHz

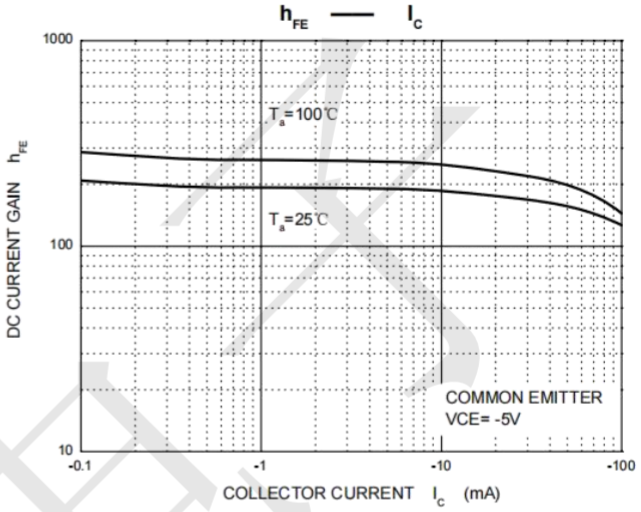
Note:

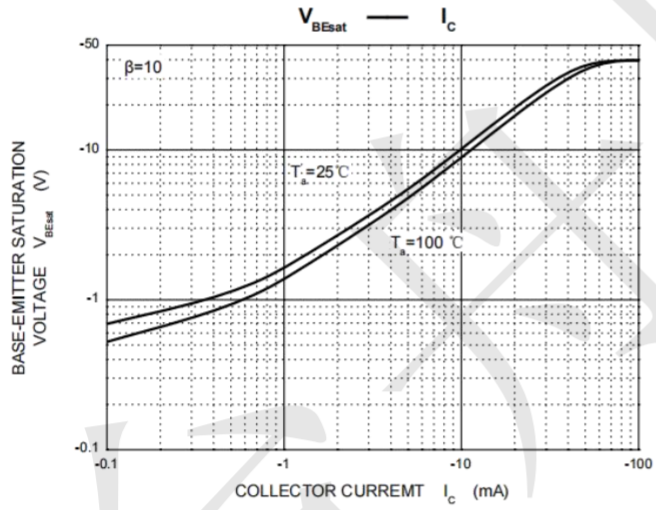
1.Characteristics of built-in transistor

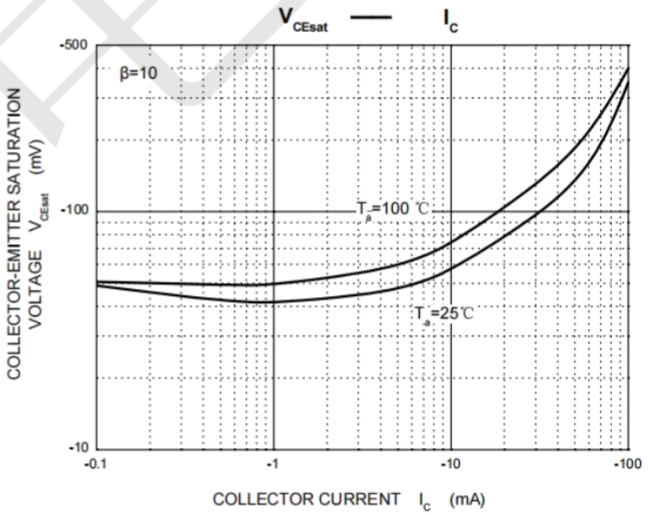
2.Each terminal mounted on a reference land

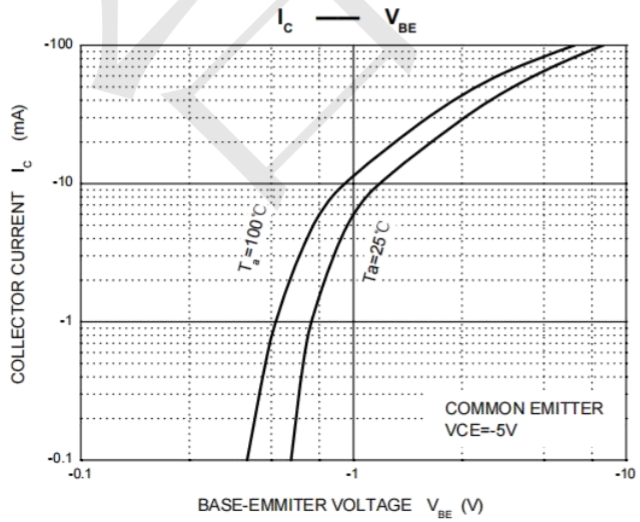
Typical Performance Characteristics(TA=25°C)

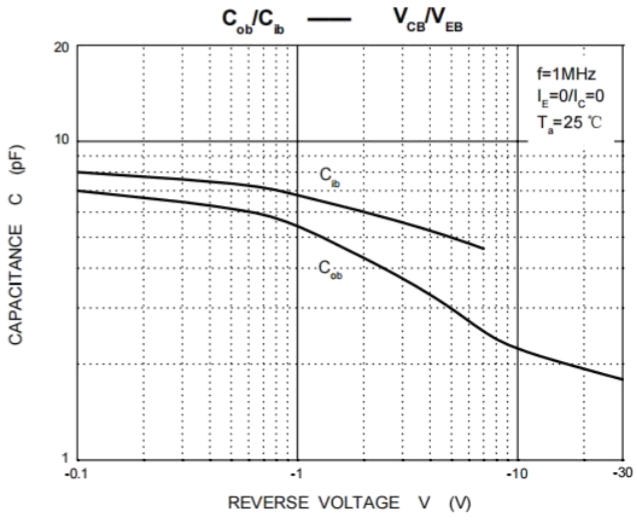






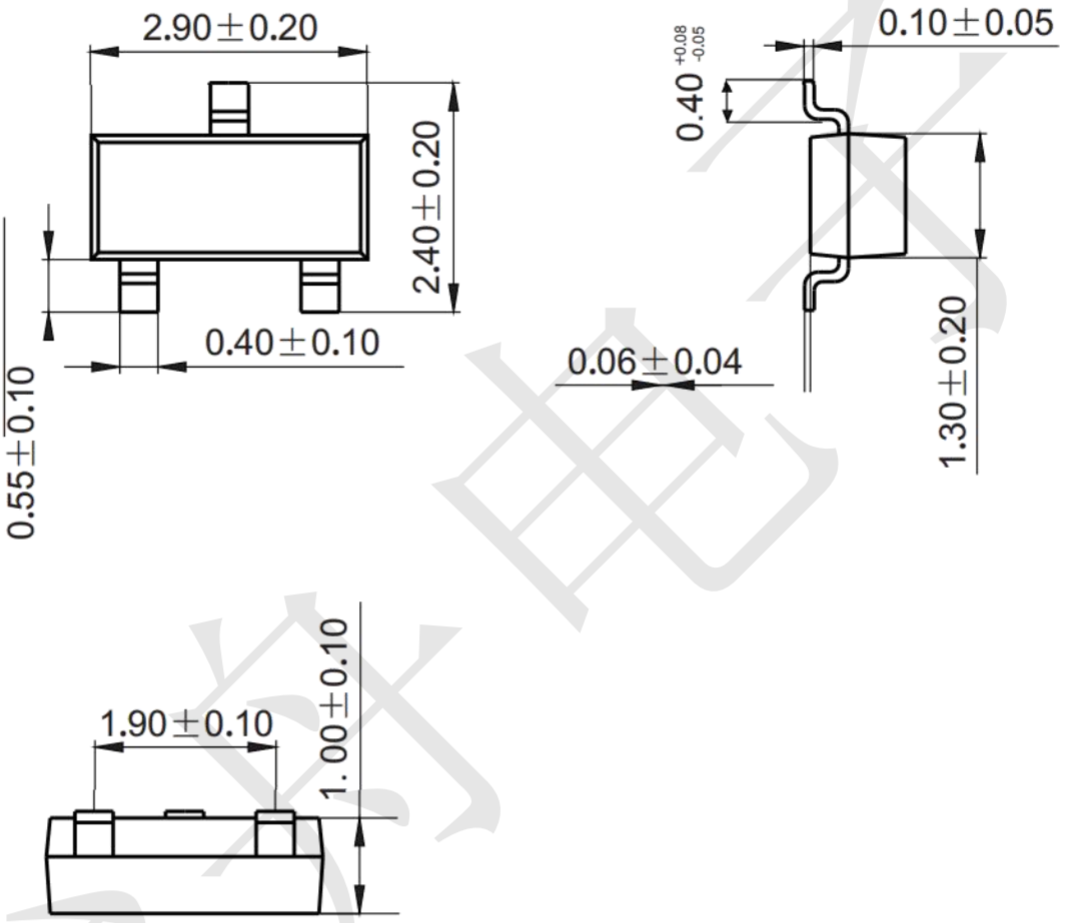






Package Outline Dimensions (unit: mm)

SOT-23



Mounting Pad Layout (unit: mm)